Contribution ID: 0 Type: not specified

Simulation of irradiated silicon p-bulk sensors

Thursday 15 November 2012 12:10 (20 minutes)

TCAD simulations of irradiated silicon p-bulk sensors have been carried out and the results have been compared to CERN 24 GeV-p irradiated n-in-p diodes.

The simulations' results are in good agreement with measured data and allow for realiable predictions on future detectors.

Primary author: BOMBEN, Marco (Univ. P. et Marie Curie (Paris VI) (FR))

Co-author: MARCHIORI, Giovanni (Univ. P. et Marie Curie (Paris VI) (FR))

Presenter: BOMBEN, Marco (Univ. P. et Marie Curie (Paris VI) (FR))

Session Classification: Detector Characterization and Simulations

Track Classification: RD50/PPS session (Friday morning)